



PATENT  
Attorney Docket No. ASC-022CPC1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S):        *Wu et al.*  
SERIAL NO.:        10/603/852        GROUP NO.:        2811  
FILING DATE:        June 25, 2003        EXAMINER:        Douglas W. Owens  
TITLE:        ETCH STOP LAYER SYSTEM

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. In accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98(a)(2)(i), only copies of the non-patent publications are enclosed.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- ☐ (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- ☒ (2) after the period defined in (1) but before the mailing date of a **final action** or a notice of **allowance** under 37 C.F.R. 1.311, and
- ☐ the requisite Statement is below, **OR**
- ☒ the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or

- ☐ (3) after the mailing date of a **final action** or **notice of allowance** but before the payment of the **issue fee, AND**
- ☐ the requisite Statement is below, **AND**
- ☐ the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

#### STATEMENT


As required under 37 C.F.R. 1.97(e), Applicant(s), through the undersigned, hereby state either that [check the appropriate space only if either (2) or (3) is checked on the previous page and the Statement is required]:

- ☐ 1. Each item of information contained in the Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application **not more than three months** prior to the filing of the Information Disclosure Statement; or
- ☐ 2. No item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this Statement after making reasonable inquiry, no item of information contained in the Information Disclosure Statement was known to **any individual** designated in 37 C.F.R. 1.56(c) **more than three months** prior to the filing of the Information Disclosure Statement.

Respectfully submitted,

Date: July 20, 2005  
Reg. No. 44,381

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Fax No.: (617) 523-1231

  
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FORM PTO - 1449

SUPPLEMENTAL INFORMATION  
DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-022CPC1

APPLICANT(S): Wu *et al.*

SERIAL NO.: 10/603,852

FILING DATE: June 25, 2003

GROUP: 2811

## U.S. PATENT DOCUMENTS

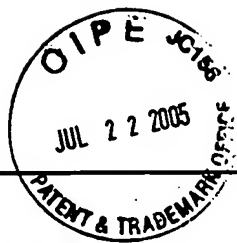
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A249	2002/140031 A1	10/03/2002	Rim			
	A250	2003/003679 A	01/02/2003	Doyle <i>et al.</i>			
	A251	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A252	5,548,128	08/20/1996	Soref <i>et al.</i>			
	A253	5,607,876	03/04/1997	Biegelsen <i>et al.</i>			
	A254	5,906,951	05/25/1999	Chu <i>et al.</i>			
	A255	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A256	6,372,593 B1	04/16/2002	Hattori <i>et al.</i>			
	A257	6,489,639	12/03/2002	Hoke <i>et al.</i>			
	A258	6,521,041	02/18/2003	Wu <i>et al.</i>			
	A259	6,591,321	07/08/2003	Arimilli <i>et al.</i>			11/09/1999
	A260	6,597,016	07/22/2003	Yuki <i>et al.</i>			01/13/2000
	A261	6,674,150	01/06/2004	Takagi <i>et al.</i>			04/03/2002
	A262	6,689,211	02/10/2004	Wu <i>et al.</i>			06/22/2000

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B53	02-098158	04/10/1990	JP				Y	Y
	B54	06-196673	07/15/1994	JP				Y	Y

EXAMINER

DATE CONSIDERED



<b>FORM PTO - 1449</b>		<b>ATTORNEY DOCKET NO.: ASC-022CPC1</b>	
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>		<b>APPLICANT(S): Wu et al.</b>	
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		<b>GROUP: 2811</b>	
<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>			
<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>		
	C146	Canaperi et al., "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with sustained epitaxial films", IBM, USA (2002) (abstract).	
	C147	Decision of Rejection for Japanese Patent Application Serial No. 2000-544004, August 20, 2002, 2 pages.	
	C148	Godbey et al., (1990) "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained Si <sub>0.7</sub> Ge <sub>0.3</sub> Layer as an Etch Stop," Journal of the Electrical Society, Vol. 137, No. 10 (October 1990) pp. 3219-3223.	
	C149	Huang et al., (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", 2001 Symposium on VLSI Technology, Digest of Technical Papers, pp. 57-58	
	C150	International Search Report for International Application No. PCT/US99/07849, August 16, 1999, 5 pages.	
	C151	International Search Report for International Application No. PCT/US01/46322, January 22, 2003, 4 pages.	
	C152	International Search Report for International Application No. PCT/US03/18007, January 5, 2004, 6 pages.	
	C153	Langdo et al., (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" IEEE International SOI Conference, pages 211-212 (XP002263057)	
	C154	Notice of Grounds of Rejection for Japanese Patent Application Serial No. 2000-544004, August 20, 2002, 4 pages (Japanese translation attached).	
	C155	Notification of Transmittal of the International Preliminary Examination Report for International Application No. PCT/US99/07849, July 7, 2000, 7 pages.	
	C156	Report of Reconsideration for Japanese Patent Application Serial No. 2000-544004, February 22, 2005, 6 pages (Japanese translation attached).	
	C157	Written Opinion for International Application No. PCT/US99/07849, January 13, 2000, 6 pages.	
	C158	Written Opinion for International Application No. PCT/US01/46322, January 22, 2003, 2 pages.	

<b>EXAMINER</b>	<b>DATE CONSIDERED</b>
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